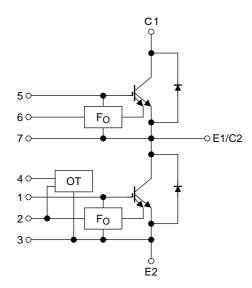
TOSHIBA IGBT Module Silicon N Channel IGBT

# MG200Q2YS60A (1200V/200A 2in1)

High Power Switching Applications
Motor Control Applications

- Integrates a complete half bridge power circuit and fault-signal output circuit in one package. (short circuit and over temperature)
- The electrodes are isolated from case.
- Low thermal resistance
- $V_{CE (sat)} = 2.4 \text{ V (typ.)}$

## **Equivalent Circuit**

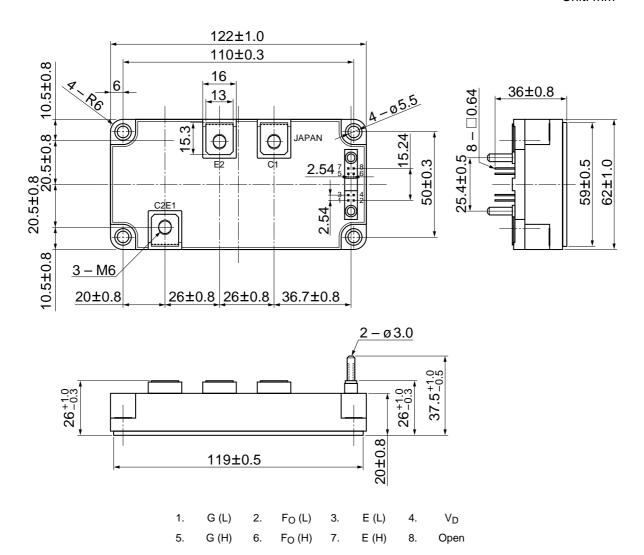


#### Signal terminal

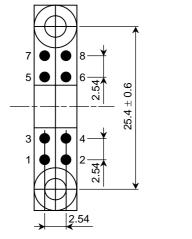
- 1. G (L) 2.  $F_O$  (L) 3. E (L) 4.  $V_D$
- 5. G (H) 6. F<sub>O</sub> (H) 7. E (H) 8. Open

## Package Dimensions: 2-123C1B

Unit: mm



## **Signal Terminal Layout**



G (L)
 F<sub>O</sub> (L)
 E (L)
 V<sub>D</sub>
 G (H)
 F<sub>O</sub> (H)
 E (H)
 Open

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Weight: 375 g

# **Maximum Ratings (Ta = 25°C)**

Stage	Characteristics	Symbol	Rating	Unit	
Inverter	Collector-emitter voltage	V <sub>CES</sub>	1200	V	
	Gate-emitter voltage	V <sub>GES</sub>	±20	V	
	Collector current	DC	IC	200	Α
	Collector current	1 ms	I <sub>CP</sub>	400	^
	Forward current	DC	l <sub>F</sub>	200	Α
	Forward current	1 ms	I <sub>FM</sub>	400	A
	Collector power dissipation (Tc =	PC	2000	W	
	Control voltage (OT)	$V_{D}$	20	V	
Control	Fault input voltage	VFO	20	V	
	Fault input current	IFO	20	mA	
Module	Junction temperature	Tj	150	°C	
	Storage temperature range	T <sub>stg</sub>	-40~125	°C	
	Operation temperature range	T <sub>ope</sub>	-20~100	°C	
	Isolation voltage	V <sub>isol</sub>	2500 (AC 1 min)	V	
	Screw torque	_	3 (M5)	N·m	

# Electrical Characteristics $(T_j = 25^{\circ}C)$

#### 1. Inverter Stage

Characteristics		Symbol	Test Condition		Min	Тур.	Max	Unit
Gate leakage current		$V_{GE} = \pm 20 \text{ V}, V_{CE} = 0$		= 0	_	_	+3/-4	mA
		I <sub>GES</sub>	$V_{GE} = +10 \text{ V}, V_{CE} = 0$		_	_	100	nA
Collector cut-off current		I <sub>CES</sub>	V <sub>CE</sub> = 1200 V, V <sub>GE</sub> = 0		_	_	1.0	mA
Gate-emitter cut-off voltage		V <sub>GE (off)</sub>	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 200 mA		6.0	7.0	8.0	V
Collector-emitter saturation voltage		V <sub>CE</sub> (sat)	VGE - 15 V,	Tj = 25°C	_	2.4	2.8	V
				Tj = 125°C	_	_	3.2	
Input capacitance		C <sub>ies</sub>	V <sub>CE</sub> = 10 V, V <sub>GE</sub> = 0, f = 1 MHz		_	15000	_	pF
Switching time	Turn-on delay time	t <sub>d (on)</sub>			0.10	_	1.00	
	Turn-off time	t <sub>off</sub>	$V_{CC} = 600 \text{ V}, I_{C} = 200 \text{ A}$		_	_	2.00	6
	Fall time	t <sub>f</sub>	$V_{GE} = \pm 15 \text{ V}, R_{G} = 10 \Omega$ (Note 1)		_	_	0.50	μS
Reverse recovery time		t <sub>rr</sub>			_	_	0.50	
Forward voltage		V <sub>F</sub>	I <sub>F</sub> = 200 A		_	2.4	2.8	V

Note 1: Switching time test circuit & timing chart

## 2. Control (Tc = $25^{\circ}$ C)

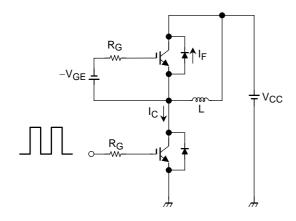
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Fault output current	ОС	V <sub>GE</sub> = 15 V	240	_	_	Α
Over temperature	ОТ	_	100	_	125	°C
Fault output delay time	t <sub>d (Fo)</sub>	$V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$	_	_	8	μS



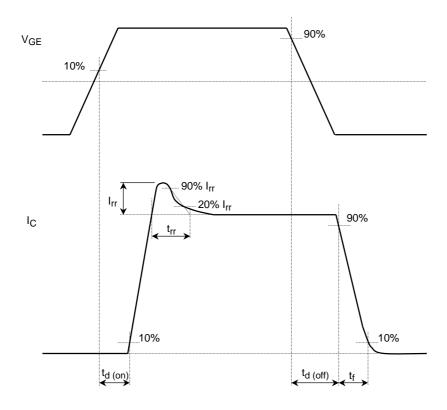
## 3. Module ( $Tc = 25^{\circ}C$ )

Characteristics	Symbol Test Condition		Min	Тур.	Max	Unit	
Junction to case thermal resistance	R <sub>th (i-c)</sub>	Inverter IGBT stage	_	_	0.062	°C/W	
Junction to case thermal resistance		Inverter FRD stage	_	_	0.136	C/VV	
Case to fin thermal resistance	R <sub>th (c-f)</sub>	With silicon compound	_	0.013	_	°C/W	

# **Switching Time Test Circuit**



# **Timing Chart**



#### Remark

#### <Short circuit capability condition>

- Short circuit capability is 6 µs after fault output signal. Please keep following condition to use fault output signal.
  - $VCC \le 750 \text{ V}$
  - $14.8 \text{ V} \le \text{V}_{\text{GE}} \le 17.0 \text{ V}$
  - RG ≥ 10 Ω
  - $T_j \leq 125$ °C

#### <Gate voltage>

• To use this product, VGE must be provided higher than 14.8 V. In case VGE is less than 14.8 V, fault signal FO may not be output even under error conditions.

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